

Atty. Docket No: 204552034000



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of: Robert DWILINSKI et al.

Serial No.: 10/519,141

Filing Date: 12/27/2004

For: PROCESS FOR OBTAINING OF BULK

MONOCRYSTALLINE GALLIUM-

CONTAINING NITRITE

Examiner: Not Yet Assigned

Group Art Unit: 2828

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

MS Amendment Commissioner for Patents P.O. Box 1450 Alexandria, Virginia 22313-1450

Dear Sir:

Pursuant to 37 C.F.R. §1.97 and § 1.98, Applicants submit for consideration in the above-identified application the documents listed on the attached Form PTO/SB/08a/b. Copies of foreign documents and non-patent literature are submitted herewith. The Examiner is requested to make these documents of record.

This Supplemental Information Disclosure Statement is submitted before mailing of a first Office Action on the merits; accordingly, no fee or separate requirements are required.

Applicants would appreciate the Examiner initialing and returning the Form PTO/SB/08a/b, indicating that the information has been considered and made of record herein.



Application No: 10/519,141

1

Atty. Docket No: 204552034000

The information contained in this Supplemental Information Disclosure Statement under 37 C.F.R. § 1.97 and § 1.98 is not to be construed as a representation that: (i) a complete search has been made; (ii) additional information material to the examination of this application does not exist; (iii) the information, protocols, results and the like reported by third parties are accurate or enabling; or (iv) the above information constitutes prior art to the subject invention.

In the unlikely event that the transmittal form is separated from this document and the Patent Office determines that an extension and/or other relief (such as payment of a fee under 37 C.F.R. § 1.17 (p)) is required, Applicants petition for any required relief including extensions of time and authorize the Commissioner to charge the cost of such petitions and/or other fees due in connection with the filing of this document to **Deposit Account No. 03-1952** referencing 204552034000.

Dated: October 13, 2005

Respectfully submitted,

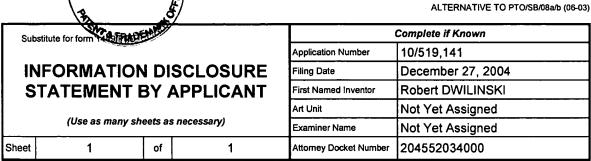
Raj S

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U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No.1	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear

FOREIGN PATENT DOCUMENTS							
Examiner Initials*	Cite No.1	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear		
		Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)				T ⁶	
	1.	WO-02/101120-A2	12-19-2002			1	

*EXAMINER: Initial if information considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. ¹ Applicant's unique citation designation number (optional). ² See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ¹ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document of Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁴ Applicant is to place a check mark here if English language Translation is attached.

NON PATENT LITERATURE DOCUMENTS					
Examiner Initials	Cite No.1	manazina injirnal sanal symposijim catalog atc.) data nagalsi yojijma-issija nijmparisi nijniishar			
	2.	T. Inoue et al. (2001) "Growth of Bulk GaN Single Crystals by the Pressure-Controlled Solution Growth Method," <i>Journal of Crystal Growth</i> 229, pp. 35-40			
	3.	M. K. Kelly et al. (1996) "Optical Patterning of GaN Films," <i>Apply. Phys. Lett.</i> 69(12), pp. 1749-1751			
	4.	W. S. Wong et al. (1999) "Fabrication of Thin-Film InGaN Light-Emitting Diode Membranes by Laser Lift-Off," <i>Applied Physics Letters</i> 75(10), pp. 1360-1362			
	5.	S. Porowski et al. (1993) "Prospects for High-Pressure Crystal Growth of III-V Nitrides," Inst. Phys. Conf. Ser. No. 137, Chapter 4, pp. 369-372			

^{*}EXAMINER: Initial if information considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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